

YJ Planar Schottky Barrier Diode Die Specification

40V 0.5A, 25mil, Schottky barrier diode die based on silicon planar process
Part No.: PSB025L040AS-180A

Main Products Characterstics

- Average forward current: IF(AV) = 0.5 A
- Maximum operating junction temperature: Tj = 125 °C
- Top metal: AL

Maximum Ratings

Static Electrical Characteristics (Ta = 25°C)

IF = 0.5 A
Pulse Test: tp = 300 μs, δ ≤ 2%

Device Schematics and Outline Drawing

Die Thickness *
Die Size **
Top Metal Pad
Active Area
Top Metal
Back Metal
Note: 1 * : Also can offer device with 10.5 mils thickness
2 **: Cutting street width is around 1.5 mils

Important Notice

Specification apply to die only. Actual performance may degrade when assembled.

YangleElectronics does not guarantee device performance after assembly.

Recommended Storage Environment:

Store in original container, in dessicated nitrogen, with no contamination.